

S4D15120A S4D15120H 1200V SiC POWER SCHOTTKY RECTIFIERS



Description

S4D15120A/S4D15120H are SiC Schottky rectifiers packaged in TO-220AC(TO-220-2)/TO-247AC(TO-247-2) case. The devices are high voltage Schottky rectifiers that have very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D15120A/S4D15120H are ideal for energy sensitive, high frequency applications in challenging environments.

Circuit Diagram



Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	1200	V
Average Rectified Forward Current	I _{F(AV)}	T _C =150°C	15	A
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	10ms, Half Sine pulse, T _J =25°C	100	A
Repetitive Peak Forward Surge Current	I _{FRM}	10 ms, Half Sine pulse, T _J =25°C	68	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 15A, Pulse, T _J = 175 °C	2.2	3.0	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	35	200	uA
	I _{R2}	@V _R = rated V _R T _J = 175 °C	120	300	uA
Junction Capacitance	C _T	VR=0V, T _J =25°C, f=1MHz	1200	-	pF

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	S4D15120A	S4D15120H	Units
Junction Temperature	T _J	-55 to +175		°C
Storage Temperature	T _{stg}	-55 to +175		°C
Maximum Thermal Resistance Junction to Case	R _{qJC}	1.7	0.61	°C/W

Ordering Information

Device	Package	Shipping
S4D15120A	TO-220AC(TO-220-2)	50pcs / tube
S4D15120H	TO-247AC(TO-247-2)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Ratings and Characteristics Curves

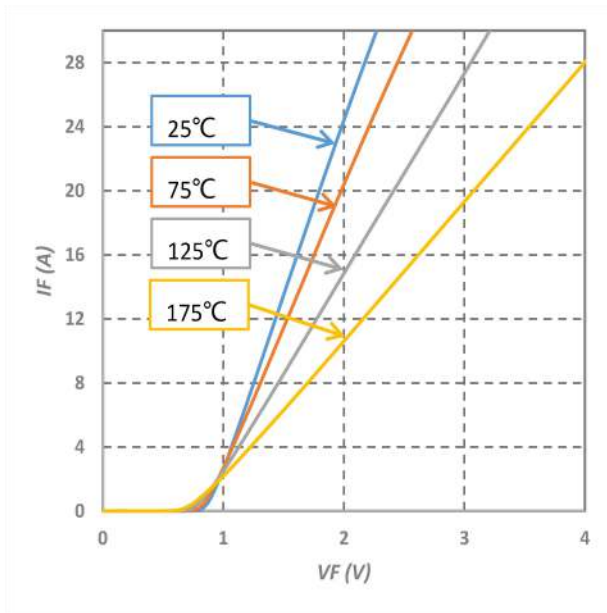


Fig.1-Typical Forward Voltage Characteristics

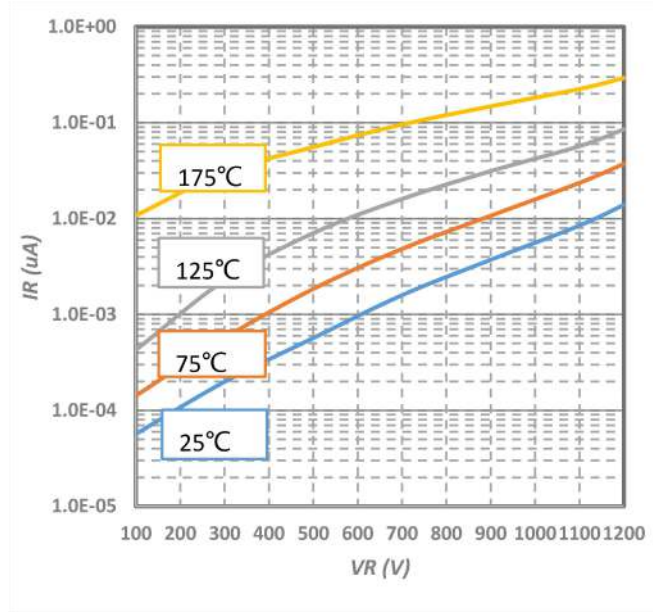


Fig.2-Typical Reverse Characteristics

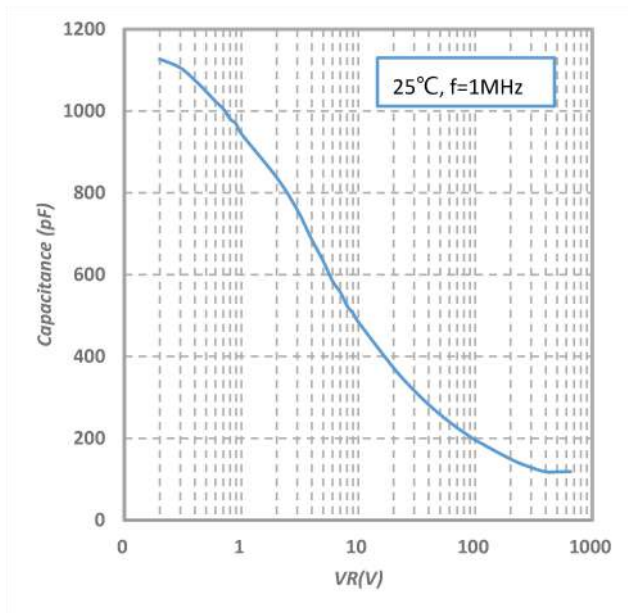
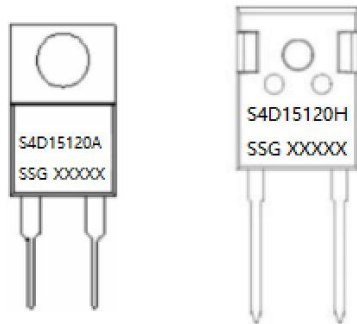


Fig.3-Capacitance vs. Reverse Voltage

Marking Diagram

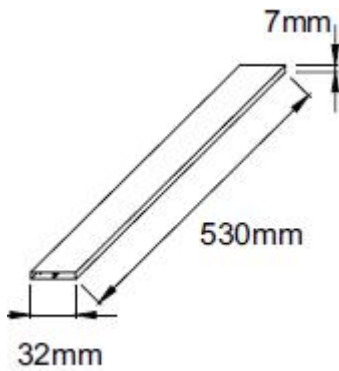


Where XXXXX is YYWWL

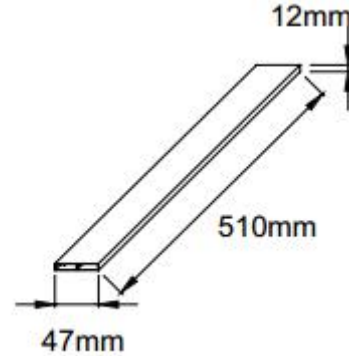
S4D = Device Type
A/H = Package type
15 = Forward Current (15A)
120 = Reverse Voltage (1200V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Tube Specification

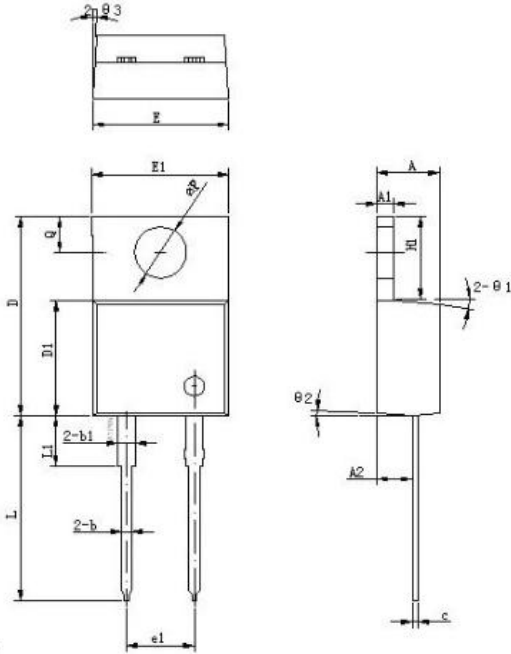


TO-220AC(TO-220-2)



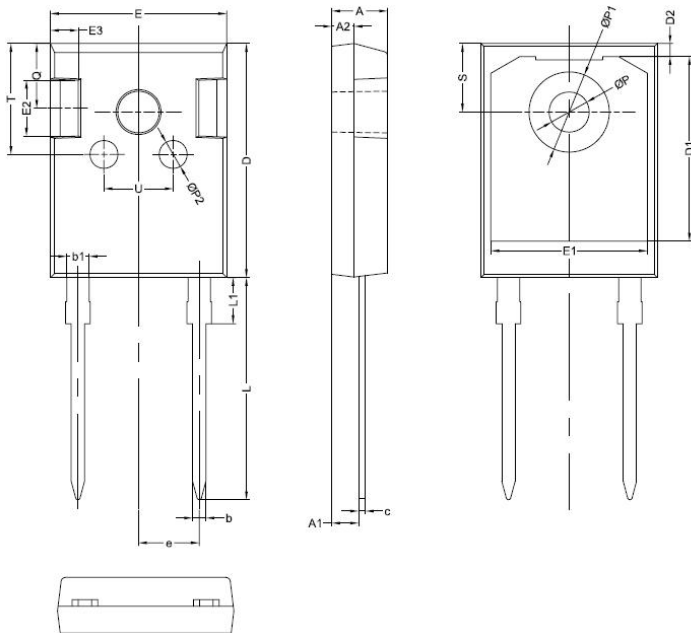
TO-247AC(TO-247-2)

Mechanical Dimensions TO-220AC(TO-220-2)



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.64	14.94	15.24
D1	8.55	8.70	8.90
E	10.01	10.16	10.31
E1	9.98	10.18	10.38
e1		5.08	
H1	6.04	6.24	6.44
L	13.00	13.86	14.08
L1		3.80	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
Θ1		5°	
Θ2		4°	
Θ3		4°	

Mechanical Dimensions TO-247AC(TO-247-2)



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	



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